NEC

PNP SILICON POWER TRANSISTOR **2SB1151**

DESCRIPTION

The 2SB1151 is a Low $V_{\text{CE(sat)}}$ transistor which has a large current capability and wide SOA.

It is suitable for DC-DC converter, or driver of solenoid or motor.

FEATURES

Low Collector Saturation Voltage.

 $V_{CE(sat)} = -0.14 \text{ V TYP.}$ (@ $I_C/I_B = -2.0 \text{ A}/-0.2 \text{ A}$)

• Large Current.

 $I_{C(DC)} = -5.0 \text{ A}, I_{C(pulse)} = -8.0 \text{ A}$

- High Total Power Dissipation. : P_T = 1.3 W
- Complementary to 2SD1691.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

 V_{CBO}

Maximum Power Dissipations

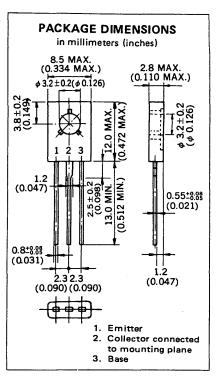
Total Power Dissipation ($T_a = 25 \,^{\circ}\text{C}$) 1.3 W Total Power Dissipation ($T_c = 25 \,^{\circ}\text{C}$) 20 W

Collector to Base Voltage

Maximum Voltages and Currents (T_a = 25 °C)

V_{CEO}	Collector to Emitter Voltage	-60	٧
V_{EBO}	Emitter to Base Voltage	-7.0	٧
I _{C(DC)}	Collector Current	-5.0	Α
I _{C(pulse)} *	Collector Current	-8.0	Α
I _{B(DC)}	Base Current	-1.0	Α

^{*} PW \leq 10 ms, Duty Cycle \leq 50 %



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
VCE(sat)**	Collector Saturation Voltage		-0.14	-0.3		I _C = -2.0 A, I _B = -0.2 A
V _{BE(sat)} **	Base Saturation Voltage		-0.9	-1.2	V	$I_C = -2.0 \text{ A}, I_B = -0.2 \text{ A}$
hFE1 **	DC Current Gain	60			-	$V_{CE} = -1.0 \text{ V}, I_{C} = -0.1 \text{ A}$
hFE2**	DC Current Gain	100	200	400	-	$V_{CE} = -1.0 \text{ V, } I_{C} = -2.0 \text{ A}$
hFE3**	DC Current Gain	50			-	$V_{CE} = -2.0 \text{ V, I}_{C} = -5.0 \text{ A}$
СВО	Collector Cutoff Current			-10	μΑ	$V_{CB} = -50 \text{ V, } I_E = 0$
IEBO	Emitter Cutoff Current			-10	μΑ	$V_{EB} = -7.0 \text{ V, I}_{C} = 0$
ton	Turn On Time		0.15	1.0	μs	
t _{stg}	Storage Time		0.78	2.5	μs	$(I_C = -2.0 \text{ A}, I_{B1} = -I_{B2} = 0.2 \text{ A})$ $(R_L = 5.0 \Omega, V_{CC} = -10 \text{ V})$
t _f	Fall Time		0.18	1.0	μs	/ UF - 2.0 25' ACC = -10 A

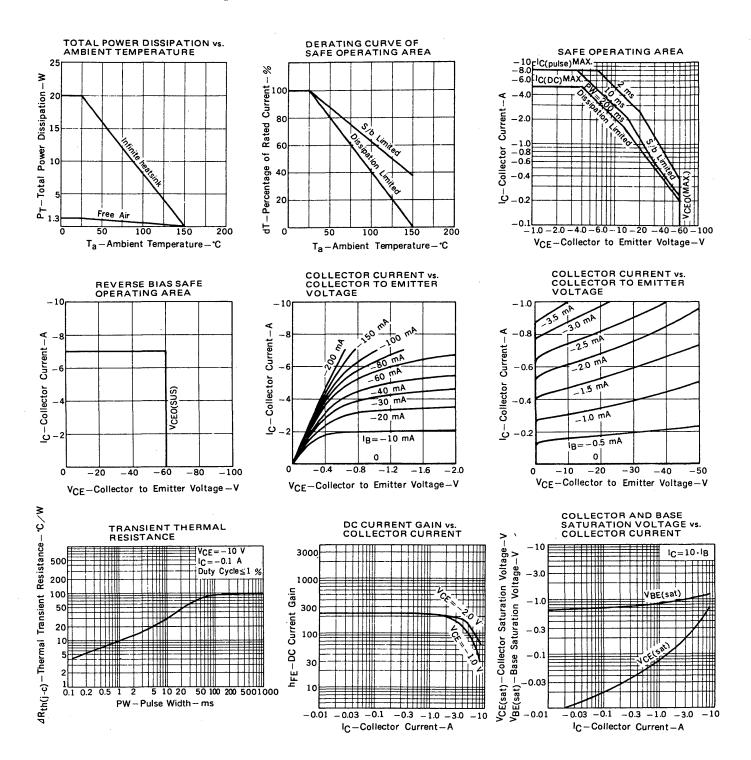
^{**} PW \leq 350 μ s, Duty Cycle \leq 2 %

Classification of hFE2

Rank	M	L	К
Range	100 to 200	160 to 320	200 to 400

Test Conditions: $V_{CE} = -1.0 \text{ V}$, $I_{C} = -2.0 \text{ A}$

TYPICAL CHARACTERISTICS (Ta = 25 °C)



This datasheet has been downloaded from:

www. Data sheet Catalog.com

Datasheets for electronic components.